

Form PTO-1349

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
M122-1531SERIAL NO.  
09/755,673

SEP 30 2004

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Leonard Forbes et al.FILING DATE  
January 5, 2001GROUP  
2823

## U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
K.N.	AA	5,605,857	02/97	Jost et al	437	760	Feb. 22, 1995
K.N.	AB	5,985,731	11/99	Weng et al	438	396	Aug. 17, 1998
K.N.	AC	6,395,650	05/02	Callegari et al	438	785	Oct. 23, 2000
	AD						
	AE						
	AF						
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## FOREIGN PATENT DOCUMENTS

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	AM							
	AN							
	AO							
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## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER

*Khrenmeyer*

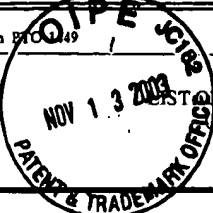
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K.N.	AM	JP200058777A	02/00	Japan - electronic translation and abstract			X
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Form PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT-AND-TRADEMARK-OFFICE

ATTY. DOCKET NO.  
MI22:1531

SERIAL NO.  
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LIST OF ART CITED BY APPLICANT  
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APPLICANT  
Micron Technology, Inc.

FILING DATE  
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PTO  
09/15/81  
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U.S. PATENT DOCUMENTS

*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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FOREIGN PATENT DOCUMENTS

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K.N.	AC	Abstract of: Oxidation of Sintered Aluminum Nitride at Near-ambient temperatures; Dutta, I.; Mitra, S.; Rabenberg, L.; Journal of the American Ceramic Society, Vol. 75, No. 11, pp. 3149-53, Nov. 1992
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	AG	Abstract of: Optical Measurement of Film Growth on Silicon and Germanium Surfaces in Room Air; R.J. Archer
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EXAMINER

Khuemnguyen

DATE CONSIDERED

08/16/02

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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22:1531		SERIAL NO. Filed Herewith 09/15/61	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Micron Technology, Inc.			
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U.S. PATENT DOCUMENTS								
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	AD		Some Properties of Chemically Vapor Deposited Films of $Al_2O_3$ on Silicon; E.A. Irene, V.J. Silvestri and G.R. Woolhouse; Journal of Electronic Materials, Vol. 4, No. 3, 1975; pp. 409-427					
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	AH		III-Nitride, SiC and Diamond Materials for Electronic Devices; Materials Research Society, Symposium Proceedings Vol. 423; April 8-12, 1996, San Francisco, CA; pp. 667-672					
	AI		Electrochemical Behaviour of AlN Films Prepared by Reactive Cathodic Sputtering; F. Vacandio, Y. Massiani, P. Gravier, L. Fedrizzi and D. Brida; Materials Science Forum; Vols. 289-292 (1998) pp. 689-697; 1998 Trans Tech Publications, Switzerland					
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<b>LIST OF ART CITED BY APPLICANT</b> (Use several sheets if necessary)				APPLICANT Micron Technology, Inc.		
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	Document Number	Date	Country	Class	Subclass	Translation
						Yes No
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	AE		Optical Interference Coatings; Florin Abeles, Chair/Editor; Proceedings Europto Series; SPIE Vol. 2253; part 2 of 2; pp. 1275-85			
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	AH		High Quality Ta <sub>2</sub> O <sub>5</sub> Gate Dielectrics with T <sub>max</sub> < 10Å; H. F. Luan, S.J. Lee, C.H. Lee, S.C. Song, Y.L. Mao, Y. Senzaki, D. Roberts and D.L. Kwong			
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K.N.	AC	Applications of Aluminum Nitride Films Deposited by Reactive Sputtering to Silicon-on-Insulator Materials; Stefan Bengtsson, Mats Bergh, Manolis Choumas, Christian Olesen and Kjell O. Jeppson; Jpn. J. Appl. Phys. Vol. 35 (1996) Pt. 1, No. 8; pp. 4175-81					
	AD	Characteristics of AlN Thin Films Deposited by Electron Cyclotron Resonance Dual-Ion-Beam Sputtering and their Application to GHz-Band Surface Acoustic Wave Devices; Hiroshi Okano, Naoki Tanaka, Yasuhiro Hirao, Yasumi Kobayashi, Kenichi Shibata and Shoichi Nakano; Jpn. J. Appl. Phys. Vol. 33 (1994); Pt. 1, No. 5B; pp. 2957-2961					
	AE	An Aluminum Oxynitride Film; Wang Dehuang, Guo Liang; Thin Solid Films, 198 (1991) pp. 207-210					
	AF	Formation of aluminum oxynitride diffusion barriers for Ag metallization; Y. Wang and T. L. Alford; Applied Physics Letters; Vol. 74, No. 1; 4 January 1999; American Institute of Physics; pp. 52-54					
	AG	Abstract of: Simulation of Hyperthermal deposition of Si and C on SiC surfaces; Applied Physics Letters; Vol. 74, No. 1; 4 January 1999; 1999 American Institute of Physics					
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EXAMINER <i>K. Hennig</i>				DATE CONSIDERED <b>08/16/02</b>			
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K.N.	AC		Structural, Optical and Electronic Properties of Oxidized AlN Thin Films at Different Temperatures; Enam Ahmed Chowdhury et al.;				
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